

BUK9M20-60EL

Single N-channel 60 V, 13 mOhm logic level MOSFET in LFPAK33 using Enhanced SOA technology

pril 2022

Product data sheet

1. General description

Single, logic level, N-channel MOSFET in LFPAK33 using Application specific (ASFET) Enhanced SOA technology. This product has been designed and qualified to AEC-Q101 for use in linear mode in airbag applications.

2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Enhanced SOA technology for improved linear mode performance
- LFPAK copper clip package technology:
 - · High robustness and current handling capability
 - · Gull wing leads for easy AOI inspection and exceptional board level reliability

3. Applications

- · 12 V automotive systems
- · Airbag squib voltage regulator MOSFET

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	40	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	79.4	W
Static characte	ristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 15 A; T_{j} = 25 °C; Fig. 13		7.3	10.4	13	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I _D = 15 A; V _{DS} = 48 V; V _{GS} = 4.5 V; T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	9	18	nC

^{[1] 40} A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		D
3	S	source		
4	G	gate		G_(□□□□□)
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1210)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package	kage					
	Name	Description	Version				
BUK9M20-60EL	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210				

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M20-60EL	9206EL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). T_i = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	60	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	79.4	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	40	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	37	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3; Fig. 4		-	208	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain d	liode			·		
Is	source current	T _{mb} = 25 °C		-	40	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	208	Α
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 37 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 51 μs; Fig. 5	[2] [3]	-	74	mJ

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Symbol	Parameter	Conditions		Min	Max	Unit
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 60 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; Fig. 5$	[2] [3] [4]	-	37	А

- [1] 40 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.
- [4] Protected by 100% test.

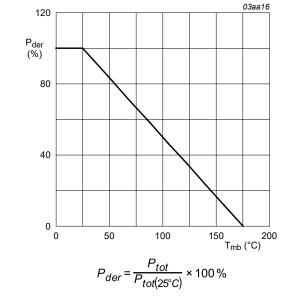
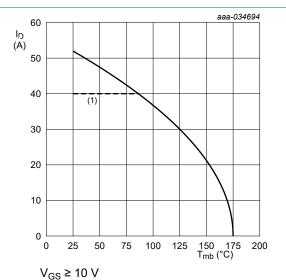
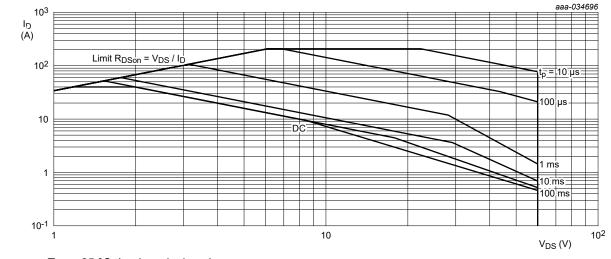


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



(1) 40 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

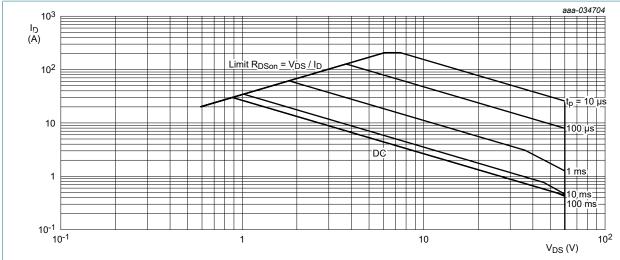
Fig. 2. Continuous drain current as a function of mounting base temperature



 T_{mb} = 25 °C; I_{DM} is a single pulse

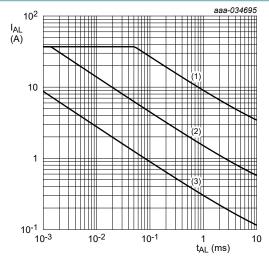
Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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T_{mb} = 125 °C; I_{DM} is a single pulse

Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

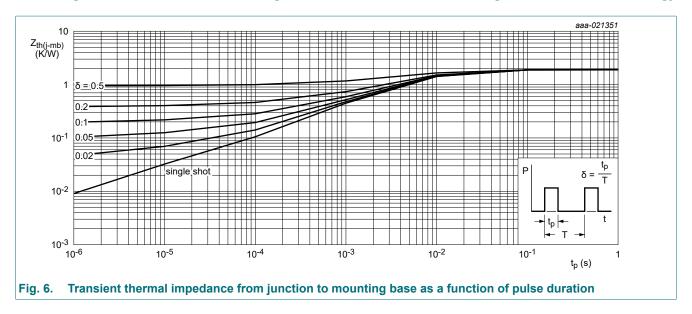
Fig. 5. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 6</u>	-	1.58	1.89	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	66	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	63	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	54	62	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 11; Fig. 12}$	1.4	1.67	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 12$	-	-	2.45	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 12	0.5	-	-	V
V _{(BR)DSS} V _{GS(th)} I _{DSS} I _{GSS} R _{DSon}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	34	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 13	7.3	10.4	13	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 105 °C; Fig. 14	11	16.4	21	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 125 °C; Fig. 14	12.2	18	23.4	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; Fig. 14	15	22.7	30	mΩ
		V_{GS} = 4.5 V; I_{D} = 15 A; T_{j} = 25 °C; Fig. 13	10.5	15	20	mΩ
		V _{GS} = 4.5 V; I _D = 15 A; T _j = 105 °C; Fig. 14	15.6	23.5	32	mΩ
		V _{GS} = 4.5 V; I _D = 15 A; T _j = 125 °C; Fig. 14	17	26	35.3	mΩ
		V _{GS} = 4.5 V; I _D = 15 A; T _j = 175 °C; Fig. 14	20.7	32	44.4	mΩ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _G	gate resistance	f = 1 MHz; T _j = 25 °C		-	1.9	-	Ω
Dynamic cl	haracteristics			'			
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 48 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	40	56	nC
		I _D = 15 A; V _{DS} = 48 V; V _{GS} = 4.5 V;		-	20	28	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	5	8	nC
Q _{GD}	gate-drain charge	V ₂₀ = 25 V: V ₂₀ = 0 V: f = 1 MHz:		-	9	18	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 17</u>		-	2101	2941	pF
C _{oss}	output capacitance			-	200	240	pF
C _{rss}	reverse transfer capacitance			-	115	158	pF
t _{d(on)}	turn-on delay time	V_{DS} = 48 V; R_L = 3.2 Ω ; V_{GS} = 5 V;		-	11	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$		-	25	-	ns
t _{d(off)}	turn-off delay time	1		-	25	-	ns
t _f	fall time			-	20	-	ns
9 _{fs}	transfer conductance	$V_{DS} = 8 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$		-	40	-	S
Source-dra	in diode						
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 18$		-	0.83	1	V
t _{rr}	reverse recovery time	$I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	29	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C; <u>Fig. 19</u>	[1]	-	33	-	nC

[1] includes capacitive recovery

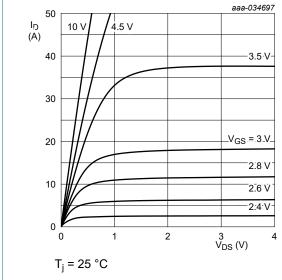


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

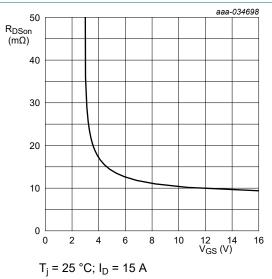


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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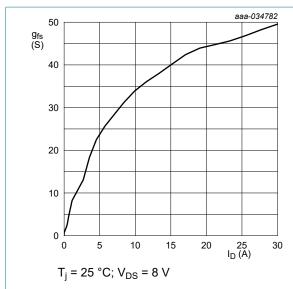


Fig. 9. Forward transconductance as a function of drain current; typical values

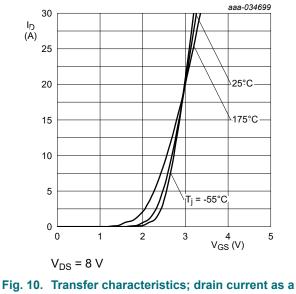


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

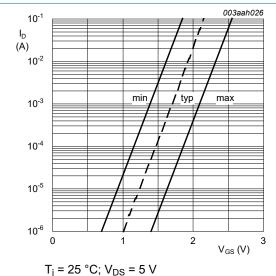


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

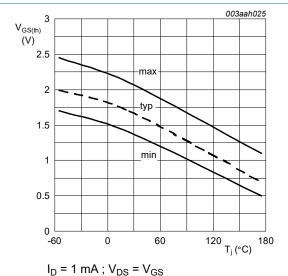


Fig. 12. Gate-source threshold voltage as a function of junction temperature

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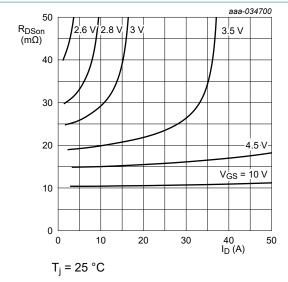


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

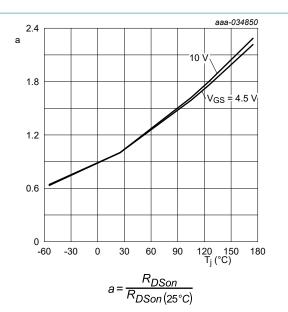


Fig. 14. Normalized drain-source on-state resistance factor as a function of junction temperature

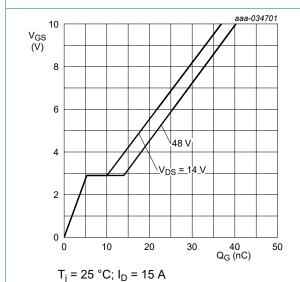


Fig. 15. Gate-source voltage as a function of gate charge; typical values

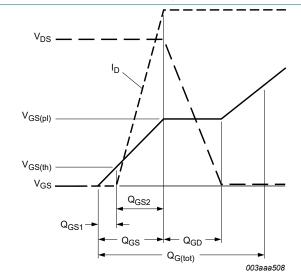


Fig. 16. Gate charge waveform definitions

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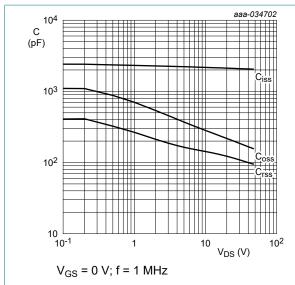
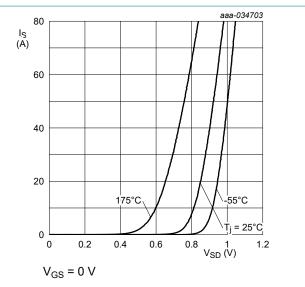


Fig. 17. Input, output and reverse transfer capacitances | Fig. 18. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

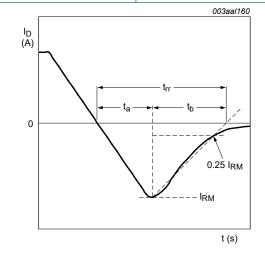


Fig. 19. Reverse recovery timing definition

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11. Package outline

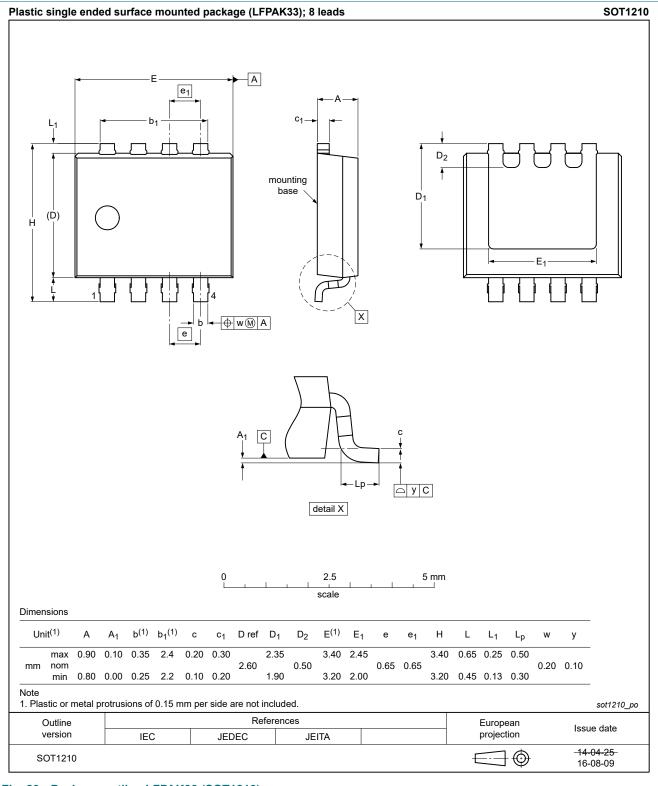


Fig. 20. Package outline LFPAK33 (SOT1210)

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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